Chen Li

List of Publications by Year
in descending order

Source: https://exaly.com/author-pdf/8522292/publications.pdf

Version: 2024-02-01

13	534	933447 10	1125743 13
papers	citations	h-index	g-index

13	13	13	352
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Atomic Layer Etching at the Tipping Point: An Overview. ECS Journal of Solid State Science and Technology, 2015, 4, N5041-N5053.	1.8	202
2	Fluorocarbon based atomic layer etching of Si3N4 and etching selectivity of SiO2 over Si3N4. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	75
3	Fluorocarbon assisted atomic layer etching of SiO2 and Si using cyclic Ar/C4F8 and Ar/CHF3 plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	74
4	Achieving ultrahigh etching selectivity of SiO2 over Si3N4 and Si in atomic layer etching by exploiting chemistry of complex hydrofluorocarbon precursors. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2018, 36, .	2.1	40
5	Characterizing fluorocarbon assisted atomic layer etching of Si using cyclic Ar/C4F8 and Ar/CHF3 plasma. Journal of Chemical Physics, 2017, 146, 052801.	3.0	35
6	Effect of the chamber wall on fluorocarbon-assisted atomic layer etching of SiO2 using cyclic Ar/C4F8 plasma. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, 040603.	2.1	24
7	Investigation of thin oxide layer removal from Si substrates using an SiO₂atomic layer etching approach: the importance of the reactivity of the substrate. Journal Physics D: Applied Physics, 2017, 50, 254006.	2.8	24
8	Impact of hydrofluorocarbon molecular structure parameters on plasma etching of ultra-low-K dielectric. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	18
9	Application of cyclic fluorocarbon/argon discharges to device patterning. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2016, 34, .	2.1	17
10	Selective atomic layer etching of HfO2 over silicon by precursor and substrate-dependent selective deposition. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, .	2.1	16
11	Electron beam injection from a hollow cathode plasma into a downstream reactive environment: Characterization of secondary plasma production and Si3N4 and Si etching. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2020, 38, 033001.	2.1	5
12	Etching of Si3N4 induced by electron beam plasma from hollow cathode plasma in a downstream reactive environment. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2020, 38, 032208.	1.2	3
13	Effect of nonvertical ion bombardment due to edge effects on polymer surface morphology evolution and etching uniformity. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	2.1	1